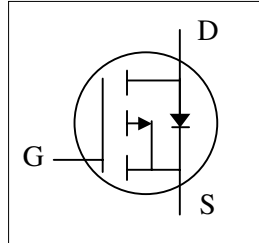




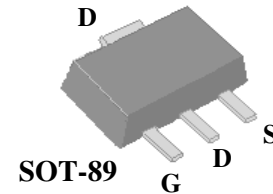
- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ Single Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	-30V
$R_{DS(ON)}$	50m $\Omega$
$I_D$	- 4.2A

## Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	- 30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ $10V^3$	- 4.2	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ $10V^3$	-3.4	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-20	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.25	W
	Linear Derating Factor	0.01	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	100	$^\circ C/W$



# AP9435GG-HF

## Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A	-	-	50	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	-	90	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-	-3	V
g <sub>fs</sub>	Forward Transconductance <sup>2</sup>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A	-	4	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA
	Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =-4A	-	8	16	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-24V	-	1.5	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	4	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =-15V	-	6.6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =-1A	-	7.7	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =-10V	-	22	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	9.3	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	570	830	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-25V	-	80	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	75	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-	-1.3	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =-4A, V <sub>GS</sub> =0V,	-	18	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=-100A/μs	-	10	-	nC

### Notes:

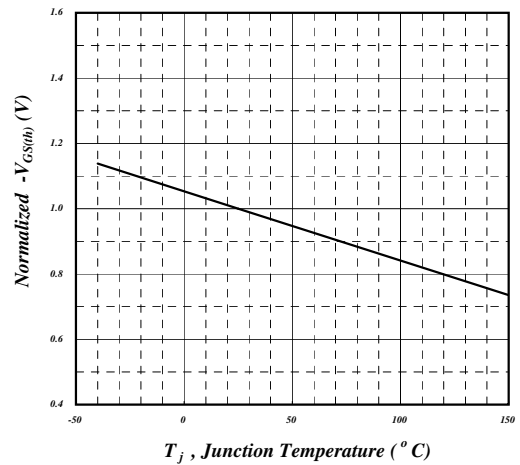
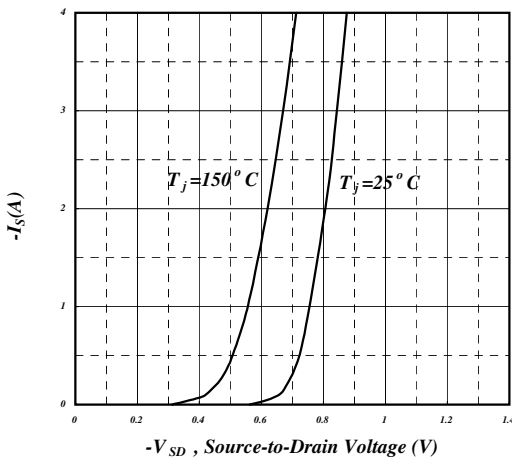
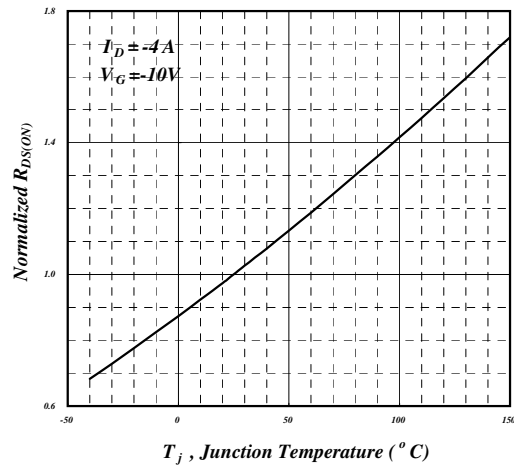
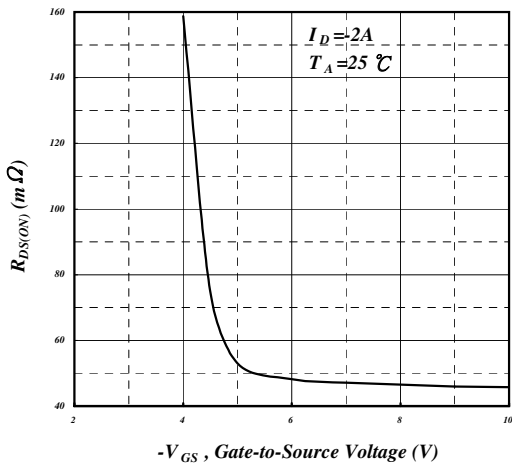
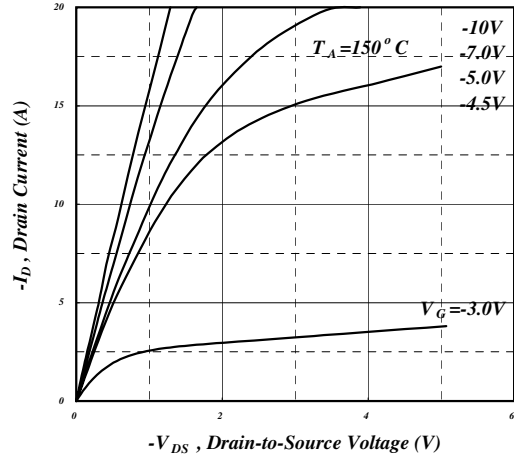
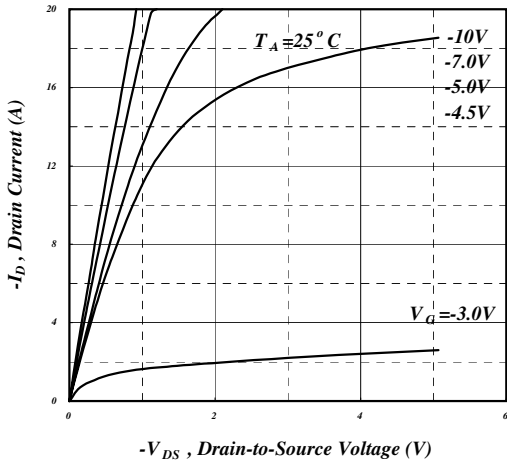
- 1.Pulse width limited by Max junction temperature.
- 2.Pulse test
- 3.Surface mount on FR4 board, t ≤ 10s.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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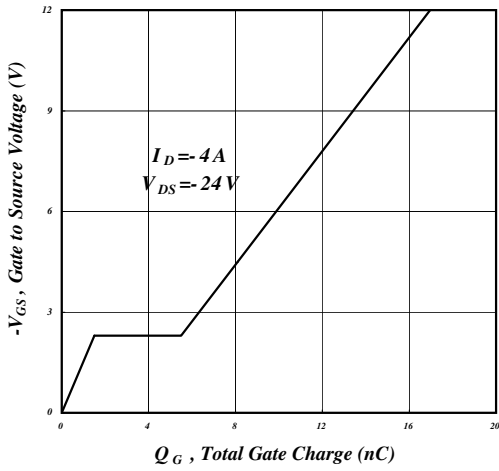


Fig 7. Gate Charge Characteristics

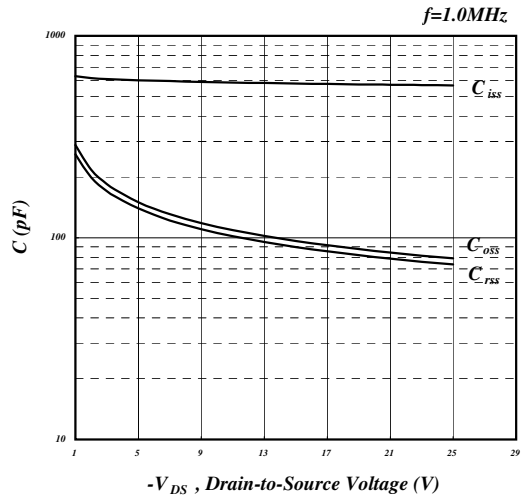


Fig 8. Typical Capacitance Characteristics

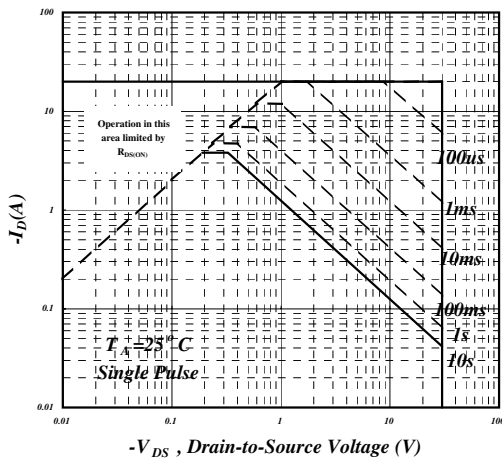


Fig 9. Maximum Safe Operating Area

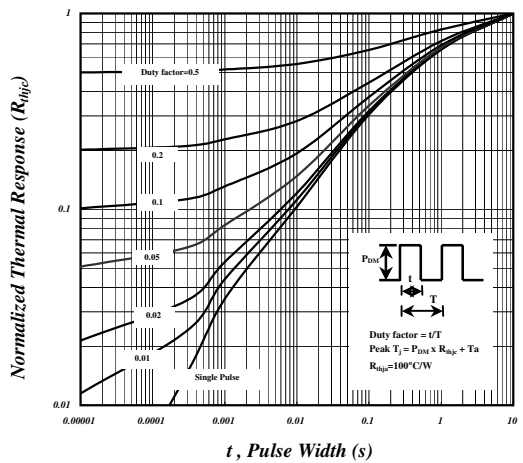


Fig 10. Effective Transient Thermal Impedance

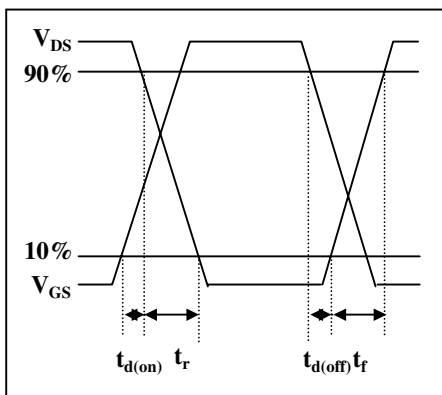


Fig 11. Switching Time Waveform

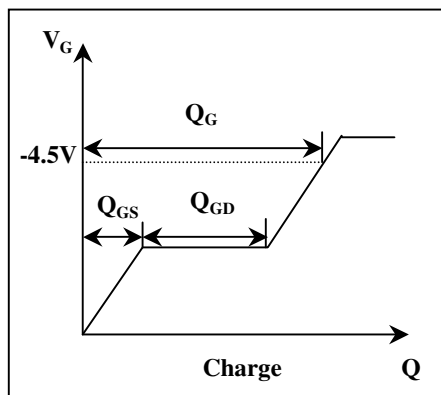


Fig 12. Gate Charge Waveform